INSTRUCTIONS

FOR

MANUAL SELECTOR

MASTR-MTS

LBI-8618 DF-9017

DESCRIPTION OF THE MANUAL SELECTOR UNIT	Page 1
DISASSEMBLY OF THE SELECTOR UNIT	Page 2
CIRCUIT ANALYSIS	Page 3
OUTLINE DIAGRAM SELECTOR UNIT	19D402801
WIRING DIAGRAM COMPONENT BOARD PL-19D402713-G1	19R620764
WIRING DIAGRAM COMPONENT BOARD PL-19D402713-G2	19R620763
WIRING DIAGRAM COMPONENT BOARD PL-19D402713-G3	19C311074
PARTS LIST (Refer to back of Wiring Diagrams)	
DECODER PL-19D402575-G1	LBI-8597
INTERCONNECTION DIAGRAM	19R620762



MANUAL SELECTOR UNIT

DESCRIPTION

The Selector unit is located in the rear section of the MTS Radio Unit. Figure 1 shows the mounting position with the cover removed. The Selector is made up of two circuit boards that are mounted back to back in the center of the wrap around chassis with access to the component sides. The circuits are described below and on the following pages. The Decoder Board PL-19D402575-G1 is mounted on the top for easy access to the number strapping jack field. Information on how to set up a number or change numbers for the Mobile are given in the Decoder instructions. The second board is Component Board PL-19D402713-G1, or 2 or 3 depending on the facilities included in the Mobile.

The function of each of the circuit boards is as follows:

- 1. Component Board PL-19D402713-G1 includes a 600/1500 cycle Tone Detector, a Control Logic circuit, Channel Switches, and an Audio Equalizer circuit for use with the carbon microphone. The Tone Detector converts the incoming 600 and 1500 cps tones to positive and negative shifts in voltage for the Decoder. The Control Logic accepts an input from the Decoder on receipt of the proper number and controls the Sounder and Call Light. When the call is completed it provides control of the circuits to reset the Mobile for receipt of other calls.
- 2. Component Board PL-19D402713-G2 includes the same circuits but in addition includes a Channel Search and Search Diode Matrix circuit. This Board working with the Reverting Board of the Control Unit provides the Search function for the Unit. When 600/1500 cps signalling appears on a channel the search is held until the signalling is complete. If the call is for another mobile the search will be resumed. If the call is for the mobile unit the channel is held.
- 3. Component Board PL-19D402713-G3 provides only the carbon microphone and Audio Equalizer circuits and the Oscillator switching circuits. The board when used limits the facilities available to Manual Selection of channels.
- 4. Decoder PL-19D402575-Gl accepts incoming voltage shifts and counts the transitions, stores them until the bit train is complete, and stores the digits when correct. When the number is correct it triggers the Control Logic Board. If the called number is incorrect the call will be dropped. The Unit call number is determined by the strapping on the number jackfield.

The interconnections between the circuit boards are shown on Interconnection Diagram 19R620762 along with the connections to the rest of the Mobile Unit.

DISASSEMBLY OF THE SELECTOR

To service the selector from the top or bottom the unit must be removed from the frame and the cover removed from the rear of the unit. The procedure is as follows:

- 1. Unlock the Radio Unit, pull the handle down and slide the unit out of the mounting frame.
- 2. Remove the screws on the top and bottom holding the rear cover in place.
- 3. The circuit boards are exposed and can be serviced except for servicing of the printed wiring. If the printed wiring must be exposed the mounting screws holding the two boards must be removed.

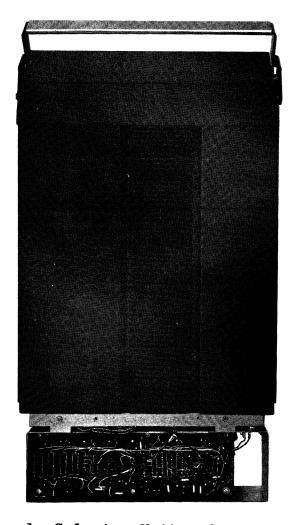


Figure 1 Selector Unit - Cover Removed

CIRCUIT ANALYSIS

COMPONENT BOARD PL-19D402713-G1 thru 3

The three groups of this board work in conjunction with other circuit boards in the Mobile Unit to provide control functions required in the Mobile Telephone Service. Since many of the circuits are repeated from one group to another the following discussion is arranged to cover the circuit once rather than two or three times.

Tone Detector PL-19D402713-G1 and 2

The 600/1500 cps signalling tones received by the mobile receiver are fed to J2 the input jack to the Tone Detector. These tones are coupled through C9 to the base of the buffer transistor Q1. This transistor is an emitter follower and the tones are fed through to the tone amplifier-limiter chain consisting of transistors Q2, Q3 and Q4. Transistor Q4 is in series with the primary winding of the Discriminator Transformer T1. The Discriminator Transformer is resonated to the tone frequencies used in signalling. The tones, 600 and 1500 cps, are rectified and filtered by the Discriminator bridge circuits and applied to the DC amplifier chains consisting of Q5 and Q7 and Q6 and Q8. These DC amplifiers provide trigger voltages for the Decoder. The Audio signalling tones sent out by the base station are thus converted to DC pulses that are the bit information for the Decoder and it's register, and used to stop the channel search.

The jack connections for this portion of the board are as follows:

+10 volts is connected through J1

A- is connected through J5

Tone input is through J2

600 cps trigger output is through J3

1500 cps trigger output is through J4.

The Decoder analysis is covered in LBI-8597 consequently it will not be covered here. As mentioned above the Decoder is provided with DC pulses that are used to trigger the bit and digit counters to obtain the called number. When the number is correct the Decoder returns a positive voltage to J14 on the component board and the Control Logic circuits.

Control Logic PL-19D402713, Gl and 2

When the Decoder is decoded by receipt of the proper bit information from the Tone Detector it returns a positive voltage to the Control Logic circuit at J14. A positive voltage applied at this point performs two functions:

- 1. The Ringer Driver Amplifier Q10 conducts resulting in the conduction of Q9, the Sounder switch. This results in positive voltage being applied to the Sounder through J12.
- 2. The positive voltage from the Decoder also causes Q11 to conduct. When Q11 conducts Q12 is turned off and Q13 is turned on. This results in the turning on of the switching transistors Q14 and

Q15. These two transistors serve as a switch for the call light in the control unit. When they conduct the call light is illuninated indicating the receipt of a call for the mobile.

The removal of the handset from the cradle results in a number of control functions. The Flip-Flop circuit composed of Q12 and Q13 resets so Q12 conducts. This resets the call light circuit so the light is extinguished. The Decoder is reset by the application of a negative shift to J16 and this in turn removes the ringing voltage from the Sounder by turning the Ringer Drive Amplifier off. The removal of the Handset from it's hanger also results in the application of a negative shift to the negative OR gate on the input to the slow clock in the Channel Search circuit.

When a call remains unanswered the handset is not removed from the cradle consequently the Decoder is not reset by actuating the hookswitch. Under these conditions, the operator dials the digit 1 to reset the Decoder. This results in the sounder being silenced but leaves the Call Light on to indicate the fact that the mobile was called.

Channel Search PL-19D402713-G2

The Channel Search circuit consists of two clocks, two bistable counter circuits, appropriate triggers and a diode matrix circuit. In operation the clocks determine which leg of the diode matrix will be positive and select transmitter and receiver oscillators. The two bistable counters have their outputs arranged so that only one leg of the diode matrix can be positive at any given moment. This arrangement permits the selection of one transmitter and one receiver oscillator.

In the following discussion it is assumed the Revert-Non Revert switch is on Revert the receiver is ready for a call and that no call The Slow Clock operates at a ten pulse per second rate. is in process. Each 100 ms the clock provides a negative impulse to the Driver Amplifier Q29 through the coupling capacitor C24. Each negative pulse applied to the base of transistor Q29 results in the turning off of the Driver Amplifier and turning on the Trigger Q30. When Q30 fires the bistable Q31-Q32 is changed in state. The bistables operate to count the bit information provided by the Trigger under control of the Slow As the Bistable Counters operate one leg of the Search Diode Matrix is allowed to go positive at a time. The specific leg is determined by the combined outputs of the bistables back biasing two of the diodes in the series CR41-CR48. The positive voltage is supplied by the control unit to J37 in the Search condition or to J33-J36 when a specific channel is chosen as the Revert channel.

When signalling occurs the pulse shifts on the output of the Tone Detectors are used to stop the Slow Clock. The duration of the tone is sufficient to assure that the channel on which the tone appears will be the channel selected. When the clock is stopped the counting by the bistables is also stopped and the stepping from one leg of the diode matrix to the other is also stopped. One leg of the matrix, that leg representing the channel, goes positive and the Receiver Oscillator switches associated with the channel conduct. An analysis of the cirtuits involved shows that the Slow Clock has a negative OR gate with

four possible inputs. Two of the inputs are from the Tone Detectors one from the Call light circuit and the fourth from the Hookswitch circuit. In the normal sequence of receiving a call the presence of signalling results in a hold on the Slow Clock, when signalling ceases the Call Light comes on and picks up the hold on the clock. When the handset is removed from the cradle to answer the call, the hookswitch supplies a negative voltage which holds the clock off and the unit on the channel until the call is completed. If the signalling is intended for some other mobile the Call light circuit would not supply the negative required to hold the Slow Clock. In this case the search would be resumed as soon as the signalling was complete.

With the Revert-Non Revert switch on the Control Unit in the OFF position the positive voltage required for search is not present. these circumstances the control of the channel is with the Channel With a given channel selected on the switch a positive Selector Switch. voltage is supplied to one of the jacks J33-J36. Assuming channel 1 is selected the positive voltage appears at J33. This positive voltage back biases CR33 and sets up the condition where the channel 1 leg of the diode matrix can go positive when the Slow Clock cycles the bistables to provide positive voltage at CR41 and CR45. When the bistables provide the positive voltage to these diodes, the channel 1 leg goes positive and CR37 feeds this voltage to the Fast Clock Trigger Q26. The appearance of a positive voltage at this point prevents the Fast Clock from cycling. When the channel 1 leg goes positive the Receiver Oscillator switches Q35 and Q36 conduct. The channel remains selected for the duration of the Slow Clock interval. At the end of the interval the Slow Clock steps the bistables off channel 1 to the next channel. no other leg on the diode matrix is allowed to go positive, the hold on the Fast clock is removed and the Fast Clock starts to cycle. Fast Clock cycles the bistables at a high rate through the legs of the diode matrix and returns to channel 1 where the positive voltage is present which again stops the Fast Clock. The effect is that Channel 1 is locked on. The time required to rapid scan the undesired channels is so small that any signal transmitted on these channels would not be received by the mobile. If the mobile is equipped with the Speaker Option and the squelch control is set to listen to noise, the cycling of the Channel Search would be heard. Under these conditions the appearance of a transmitted signal on one of the undesired channels would be noticeable but unreadable.

One other mode of operation is used. When a call is to be initiated from the mobile the channel search circuits must lock on channel. The channel selected is determined by the Channel Selector Switch on the Control Unit. The moment the handset is removed from it's hanger a negative voltage is fed to the negative OR gate on the input of the Slow Clock. This negative voltage stops the clock and the mobile locks on to the channel that has been selected by the Channel Selector Switch. The operation is similar to that discussed above with the difference that the Clocks are inoperative and as a consequence no search is possible.

Search Strapping

When channels are to be searched the diode matrix must be connected to search the specific channels assigned. The pin plugs P1-P4 should be connected to jacks J38-J45 as required for proper operation. The connections are given in the Outline Diagram in a table.

Oscillator Switches PL-19D402713-Gl and 3

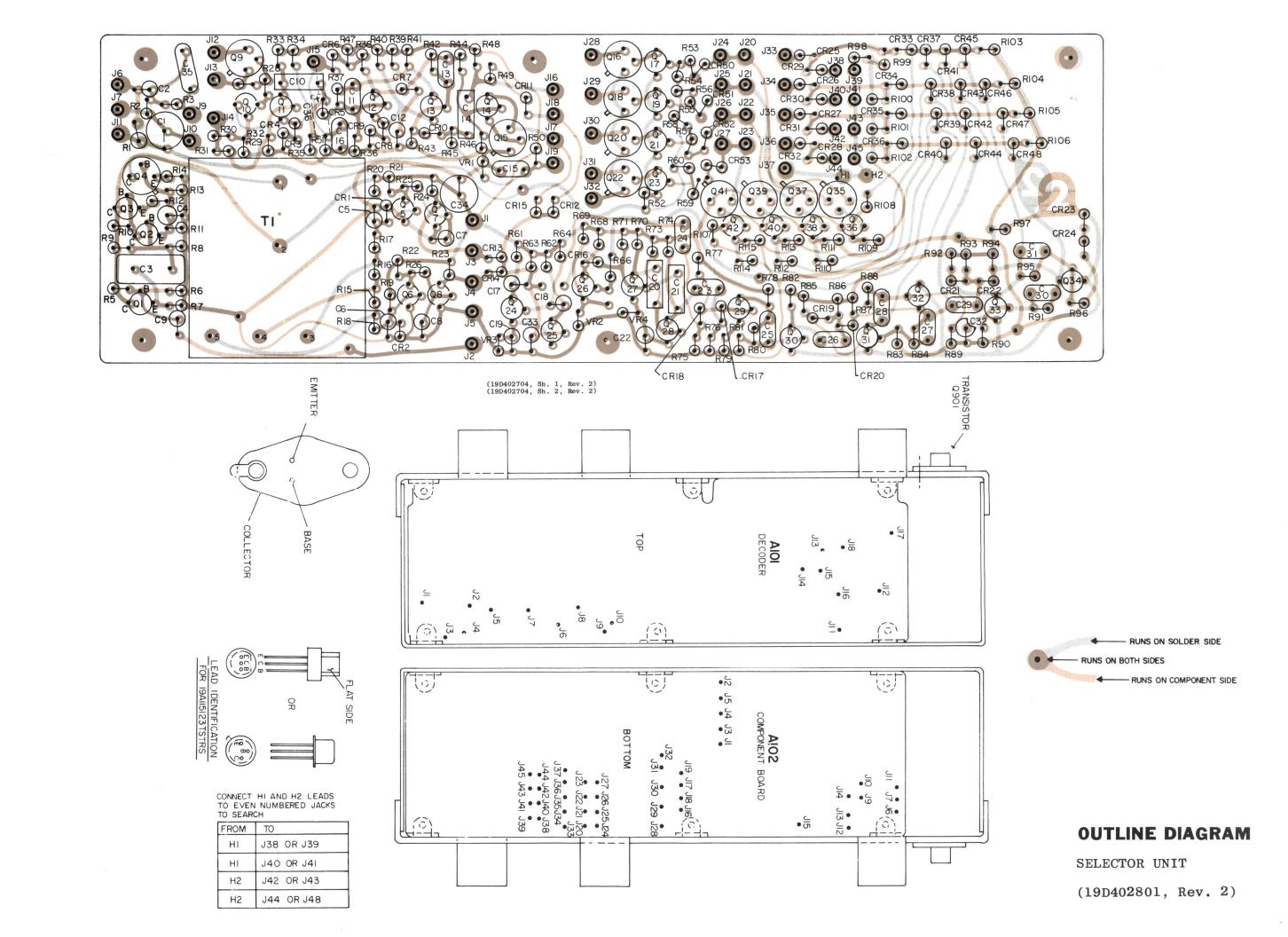
In non search systems the Channel Selector Switch channel leads are connected through to J20-J23. The positive voltage required to select the desired channel is supplied on these leads to the switching transistors Q16-Q23. The receiver associated with these boards requires a positive voltage to turn the oscillators on and the transmitter requires a battery ground. The Channel 1 transistor for the receiver is Q17 and for the transmitter Q16. Channel 2, 3, and 4 switching circuits are identical to the Channel 1 circuit consequently the circuit for channel I will be the only one discussed here. As stated above the Channel Selector Switch is connected to J20. J20 is directly connected to J24 which goes to the receiver oscillator. At the Junction of J20 and J24 diode CR50 connects through R53 to the base circuit of Q17 and to the -20 volt keyed source. With this circuit arrangement when a positive voltage is fed to J20 to select channel 1 the receiver oscillator will be activated. Since the -20 volts is only keyed when the Push-to-Talk switch is pressed the switching transistor Q17 is not turned on. When the Push-to-Talk button is pressed the -20 volts is connected to the base and completes the bias circuit for the switching transistor. When transistor Q17 conducts the transmitter oscillator switching transistor Q16 is driven into conduction resulting in the application of a ground for the transmitter oscillator. The receiver is inoperative since the Push-to-Talk relay transfers, the antenna to the transmitter and also turns off the +10 volts for the receiver.

Oscillator Switches PL-19D402713-G2

In Search systems the channel selector switches operate in much the same fashion. A second set of transistors are introduced in the circuit to permit the Search Diode Matrix channel leads to provide the positive voltage required for channel selection. In Search systems the Channel Selector Switch leads are connected to J33-J36 instead of J20-This effectively changes the channel selection from direct selection to selection through the Diode Matrix. In either the Revert or Non-Revert condition the voltage for channel selection is placed on one leg of the diode matrix. Assuming that the positive control voltage appears on the channel 1 leg switching transistor Q36 will conduct since the base circuit is completed when the voltage appears. The conduction of Q36 will result in the firing of Q35. These two transistors are directly coupled. When Q35 conducts a positive voltage appears at J20 This positive voltage turns the receiver oscillator on in the manner described above. When the Push-to-Talk button is pressed to transmit the transmitter oscillator is turned on. This sequence is described in the preceding section.

Microphone and Audio Equalizer PL-19D402713-G1, 2 and 3

The microphone used with the mobile unit in MTS combinations is a carbon microphone with relatively high output. In non-MTS applications a reluctance microphone is used. The frequency response and audio output levels of the two microphones are not identical, consequently it is desireable to provide similar responses since the receivers used in conjunction with these systems, are equipped with a standardized response characteristic. In the case of the carbon microphone it is necessary to adjust the audio input to the transmitter by inserting a network consisting of C2, R2, R3 and C35. This network de-emphasizes the low frequencies so the input to the transmitter is essentially the same as the input from a dynamic mircophone without the filter network.



- CONTROL LOGIC -

SEE APPLICABLE PRODUCTION CHANGE SHEETS IN INSTRUCTION BOOK SECTION DEALING WITH THIS UNIT, FOR DES -CRIPTION OF CHANGES UNDER EACH REVISION LETTER.

THIS ELEM DIAG APPLIES TO REV LETTER MODEL NO PL19D402713GI

WIRING DIAGRAM

COMPONENT BOARD PL-19D402713-G1

(19R620764, Rev. 2)

COMPONENT BOARD WITHOUT 600/1500 SEARCH

	COMPONENT	BOARD WITHOUT 600/1500 SEARCH 19D402713G1 REV A	Q20 Q21	19A115562P2 19A115123P1
			Q22	19A115562P2
SYMBOL	CE DADT NO	DECODIDATION	Q23	19A115123P1
21MBUL	GE PART NO.	DESCRIPTION		
			R1	3R77P202J
C1	5496267P120	Tantalum: 47 µf ±20%, 35 VDCW; sim to	R2 R3	3R152P131K 3R152P513K
		Sprague Type 150D.	R5	3R152P433J
C2	5496267P14	Tantalum: 15 μ f \pm 20%, 20 VDCW; sim to Sprague Type 150D.	and R6	
C3	19A116080P9	Polyester: 0.22 µf ±20%, 50 VDCW.	R7	3R152P202J
C4	5496267P14	Tantalum: 15 μf $\pm 20\%$, 20 VDCW; sim to Sprague Type 150D.	R8	3R152P512J
C5 thru	5496267P1	Tantalum: 6.8 µf ±20%, 6 VDCW; sim to Sprague Type 150D.	R9	3R152P472J
C9		opragate type 1000.	R10	3R152P102J
C10	19A116080P5	Polyester: .047 μf ±20%, 50 VDCW.	R11 R12	3R152P202J 3R152P511J
C11	5494481P111	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	R12	3R152P301J
C12	5496267P13	Tantalum: 2.2 μf ±20%, 20 VDCW; sim to Sprague Type 150D.	R14	3R152P161J
C13	5494481P111	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to	R15	3R152P242K
014	104112222	RMC Type JF Discap.	R16	3R152P622K
C14 C15	19A116080P5 5494481P111	Polyester: .047 µf ±20%, 50 VDCW.	R17 and	3R152P102J
and C16	J494461F111	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	R18	
C34	5496267P111	Tantalum: 68 μ f ±20%, 15 VDCW; sim to	R19	3R152P124K
		Sprague Type 150D.	R20 R21	3R152P683J 3R152P183J
C35 C36	19A116080P103 5496267P13	Polyester: .022 µf ±10%, 50 VDCW.	and R22	5 K 1 G 2 1 1 G G
CSG	3450207F13	Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D.	R23 and R24	3R152P202J
CR1 thru	19A115250P1	DIODES AND RECTIFIERS	R25 and R26	3R152P102K
CR11 CR50	19A115250P1	Silicon.	R27	3R152P472J
thru CR53			R28	3R152P182J
		JACKS AND RECEPTACLES	R29 thru	3R152P223K
Jl thru	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	R32	
J7			R33	3R152P472K
J9 thru	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	R34	3R152P222K
J32	400053054		R35	3R152P273K 3R152P153K
J37	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	R37	3R152P103J
		TRANSISTORS	R38	3R152P331J
Q1 thru	19A115889P1	Silicon, NPN; sim to Type 2N2712.	R39	3R152P473K
Q3	1		R40	3R152P222K
Q4 Q5	19A115300P2 19A115889P1	Silicon, NPN; sim to Type 2N3053. Silicon, NPN; sim to Type 2N2712.	R41	3R152P102J
thru Q8	TURITUGGSFI	orricon, NEA, Sim to Type 202/12.	R42	3R152P103J
Q9	19A115562P2	Silicon, PNP.	R43	3R152P153J 3R152P183K
Q10 thru	19A115123P1	Silicon, NPN; sim to Type 2N2712.	R45	3R152P183K
Q14			R46	3R152P153J
Q15	19A115300P2	Silicon, NPN; sim to Type 2N3053.	R47	3R152P681J
Q16	19A115562P2	Silicon, PNP.	R48	3R152P152J
Q17 Q18	19A115123P1 19A115562P2	Silicon, NPN; sim to Type 2N2712. Silicon, PNP.	R49	3R152P511J
d10	194115562P2	Silicon, PAP.	R50	3R152P222K
	1	1	11	1

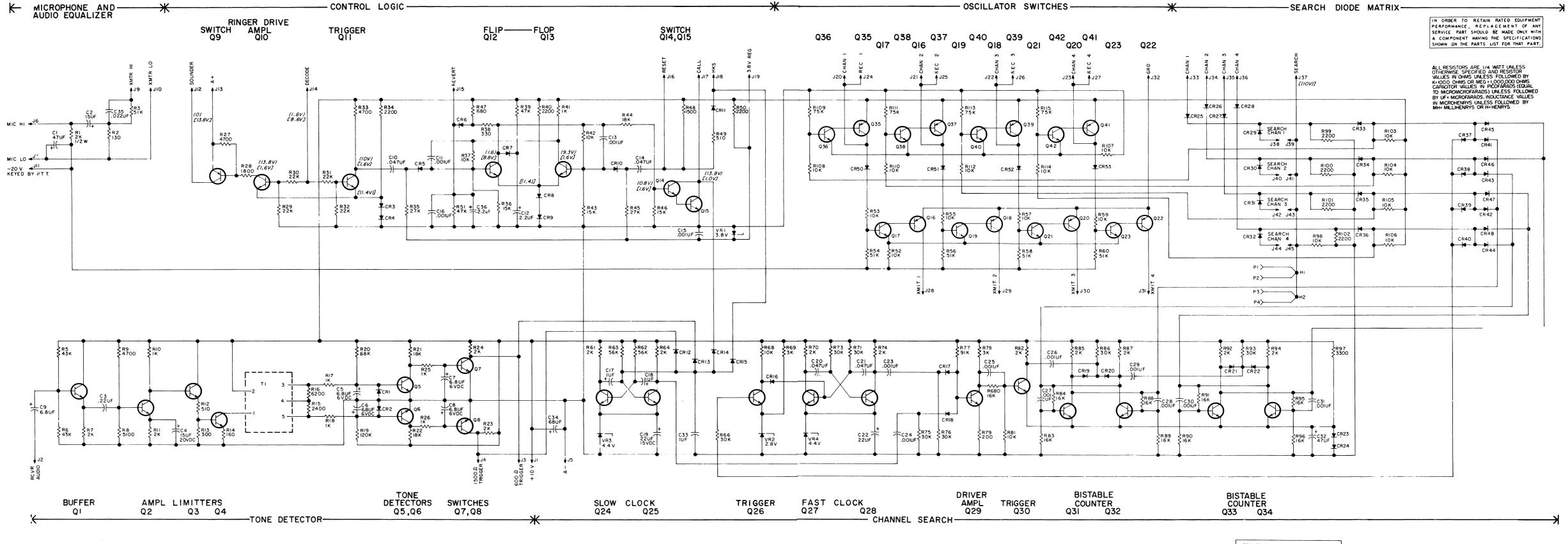
SYMB0L	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
Q19	19A115123P1	Silicon, NPN; sim to Type 2N2712.	R51	3R152P473K	Composition: 47,000 ohms $\pm 10\%$, $1/4$ w.
Q20	19A115562P2	Silicon, PNP.	R52	3R152P103J	Composition: $10,000$ ohms $\pm 5\%$, $1/4$ w.
Q21	19All5123Pl	Silicon, NPN; sim to Type 2N2712.	and R53		
Q22	19A115562P2	Silicon, PNP.	R54	3R152P513J	Composition: 51,000 ohms $\pm 5\%$, $1/4$ w.
Q23	19A115123P1	Silicon, NPN; sim to Type 2N2712.	R55	3R152P103J	Composition: 10,000 ohms $\pm 5\%$, 1/4 w.
			R56	3R152P513J	Composition: $51,000$ ohms $\pm 5\%$, $1/4$ w.
			R57	3R152P103J	Composition: 10,000 ohms $\pm 5\%$, 1/4 w.
R1	3R77P202J	Composition: 2000 ohms ±5%, 1/2 w.	R58	3R152P513J	Composition: 51,000 ohms $\pm 5\%$, $1/4$ w.
R2	3R152P131K	Composition: 130 ohms ±10%, 1/4 w.	R59	3R152P103J	Composition: 10,000 ohms $\pm 5\%$, 1/4 w.
រេ រេ	3R152P513K 3R152P433J	Composition: 51,000 ohms ±10%, 1/4 w.	R60	3R152P513J	Composition: 51,000 ohms $\pm 5\%$, 1/4 w.
	38152P4555	Composition: 43,000 ohms ±5%, 1/4 w.			
	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w.	T1		DISCRIMINATOR
	3R152P512J	Composition: 5100 ohms $\pm 5\%$, $1/4$ w.	''		19B206203G1
	3R152P472J	Composition: 4700 ohms $\pm 5\%$, $1/4$ w.			
	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.	C1	19C307114P2203G	Polystyrene: 220,000 pf ±2%, 100 VDCW.
	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w.	C2	19C307114P2203G	Polyetyrene: 100,000 pf ±2%, 100 VDCW.
	3R152P511J	Composition: 510 ohms $\pm 5\%$, $1/4$ w.		120001111110030	101,000,000 pr 120, 100 (DOIL
	3R152P301J	Composition: 300 ohms ±5%, 1/4 w.			DIODES AND RECTIFIERS
	3R152P161J	Composition: 160 ohms ±5%, 1/4 w.	CR1 thru	19A115250P1	Silicon.
	3R152P242K	Composition: 2400 ohms ±10%, 1/4 w.	CR8		
	3R152P622K	Composition: 6200 ohms ±10%, 1/4 w.			INDUCTORS
	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.	L1 L2	19C300501G410 19C300501G411	Ferrite coil. Ferrite coil.
	3R152P124K	Composition: 0.12 megohm ±10%, 1/4 w.		1903003010411	
	3R152P683J	Composition: 68,000 ohms ±5%, 1/4 w.]		VOLTAGE REGULATORS
	3R152P183J	Composition: 18,000 ohms ±5%, 1/4 w.	VR1	4036887P3	Silicon, Zener.
3R	152P202J	Composition: 2000 ohms ±5%, 1/4 w.		4036555Pl	Insulator, washer: nylon. (Used with Q4, 9, 15, 16, 18, 20, 22).
	3R152P102K	Composition: 1000 ohms ±10%, 1/4 w.			
	3R152P472J	Composition: 4700 ohms ±5%, 1/4 w.			
	3R152P182J	Composition: 1800 ohms ±5%, 1/4 w.		1	
	3R152P223K	Composition: 22,000 ohms ±10%, 1/4 w.			
	3R152P472K	Composition: 4700 ohms ±10%, 1/4 w.			
	3R152P222K	Composition: 2200 ohms ±10%, 1/4 w.			
	3R152P273K	Composition: 27,000 ohms ±10%, 1/4 w.	11	1	
	3R152P153K	Composition: 15,000 ohms ±10%, 1/4 w.			
	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	11		
	3R152P331J	Composition: 330 ohms ±5%, 1/4 w.			
	3R152P473K	Composition: 47,000 ohms ±10%, 1/4 w.			
	3R152P222K	Composition: 2200 ohms ±10%, 1/4 w.			
	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.			
	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.			
	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.			
	3k152P183K	Composition: 18,000 ohms ±10%, 1/4 w.			
	3R152P273K	Composition: 27,000 ohms ±10%, 1/4 w.			
	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.			
7 3	3R152P681J	Composition: 680 ohms ±5%, 1/4 w.			
	3R152P152J	Composition: 1500 ohms ±5%, 1/4 w.			
	3R152P511J	Composition: 510 ohms ±5%, 1/4 w.			
3RI	152P222K	Composition: 2200 ohms ±10%, 1/4 w.			
		•			

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A 19D402713G1
To prevent CALL LIGHT falsing caused by vehicle buzzer.
Added C36.



NOTES:

I. VOLTAGE MEASUREMENTS - ENCLOSED IN PARENTHESIS WERE TAKEN IN THE ON-HOOK, NON DECODED STATE.

2. VOLTAGE MEASUREMENTS ENCLOSED IN BRACKETS WERE TAKEN IN THE ON-

SEE APPLICABLE PRODUCTION CHANGE
SHEETS IN INSTRUCTION BOOK SECTION
DEALING WITH THIS UNIT, FOR DES.
CRIPTION OF CHANGES UNDER EACH
REVISION LETTER.

THIS ELEM DIAG APPLIES TO

MODEL NO REV LETTER
PLI9D402713G2 A

WIRING DIAGRAM

COMPONENT BOARD PL-19D402713-G2

(19R620763, Rev. 2)

LBI-8615A

COMPONENT BOARD WITH 600/1500 SEARCH

C1	CVMDOI	CE DART NO	DECODICTION	Q5 thru Q8
C1 5496267P120 Tantalum: 47 µf ±205, 35 VDCW; sim to Sprague Type 150D. C2 5496267P14 Tantalum: 15 µf ±205, 20 VDCW; sim to Sprague Type 150D. C3 19A116080P9 Polyester: 0.22 µf ±205, 30 VDCW. C4 5496267P14 Tantalum: 15 µf ±205, 20 VDCW; sim to Sprague Type 150D. C5 496267P14 Tantalum: 15 µf ±205, 20 VDCW; sim to Sprague Type 150D. C6 thru C7 19A116080P5 Polyester: .047 µf ±205, 50 VDCW. C10 19A116080P5 Polyester: .047 µf ±205, 50 VDCW. C11 5494481P111 Ceramic dimc: .001 pf ±205, 1000 VDCW; sim to Sprague Type 150D. C12 5496267P13 Tantalum: 2.2 µf ±205, 30 VDCW. C13 5494481P111 Ceramic dimc: .001 pf ±205, 1000 VDCW; sim to Sprague Type 150D. C14 19A116080P5 Polyester: .047 µf ±205, 30 VDCW. C15 5494481P111 Ceramic dimc: .001 pf ±205, 1000 VDCW; sim to NMC Type JF Discap. C16 19A116080P5 Polyester: .047 µf ±205, 30 VDCW. C17 5496267P17 Tantalum: 12 µf ±205, 35 VDCW; sim to Sprague Type 150D. C19 5496267P17 Tantalum: 12 µf ±205, 35 VDCW; sim to Sprague Type 150D. C20 19A116080P5 Polyester: .047 µf ±205, 35 VDCW; sim to Sprague Type 150D. C21 2 5496267P10 Tantalum: 22 µf ±205, 15 VDCW; sim to Sprague Type 150D. C22 5496267P10 Tantalum: 22 µf ±205, 15 VDCW; sim to Sprague Type 150D. C23 5496267P10 Tantalum: 22 µf ±205, 15 VDCW; sim to Sprague Type 150D. C23 5496267P10 Tantalum: 22 µf ±205, 15 VDCW; sim to Sprague Type 150D. C24 5496267P10 Tantalum: 28 µf ±205, 15 VDCW; sim to Sprague Type 150D. C25 5496267P10 Tantalum: 88 µf ±205, 15 VDCW; sim to Sprague Type 150D. C34 5496267P11 Tantalum: 68 µf ±205, 15 VDCW; sim to Sprague Type 150D. C35 19A116080P103 Polyester: .022 µf ±105, 50 VDCW. C36 5496267P11 Tantalum: 22 µf ±205, 35 VDCW; sim to Sprague Type 150D. C37 19A116080P103 Polyester: .022 µf ±205, 20 VDCW; sim to Sprague Type 150D. C38 19A116250P1 Silicon. C19A116250P1 Silicon. C19A1	SYMBOL	GE PART NO.	DESCRIPTION	
C1 5496267P120 Tantalum: 47 µf ±20%, 35 VDCW; sim to Sprague Type 150D. C2 5496267P14 Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C3 19A1608099 Polyester: 0.22 µf ±20%, 50 VDCW. C4 5496267P14 Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C5 496267P14 Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C6 Stantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C1 19A11608095 Polyester: .047 µf ±20%, 50 VDCW; sim to MAC Type JF Discap. C1 25496267P13 Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C1 35494481P111 Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to Sprague Type 150D. C1 19A11608095 Polyester: .047 µf ±20%, 50 VDCW. C1 19A11608095 Polyester: .047 µf ±20%, 50 VDCW. C1 19A11608095 Polyester: .047 µf ±20%, 50 VDCW. C1 19A11608095 Polyester: .047 µf ±20%, 1000 VDCW; sim to Sprague Type 150D. C1 19A11608095 Polyester: .047 µf ±20%, 1000 VDCW; sim to Sprague Type 150D. C1 29A96267P17 Tantalum: 1 µf ±20%, 33 VDCW; sim to Sprague Type 150D. C2 25A96267P10 Tantalum: 2.2 µf ±20%, 15 VDCW; sim to Sprague Type 150D. C2 35496267P10 Tantalum: 2.2 µf ±20%, 15 VDCW; sim to Sprague Type 150D. C2 35496267P10 Tantalum: 2.2 µf ±20%, 1000 VDCW; sim to Sprague Type 150D. C3 5496267P10 Tantalum: 2.2 µf ±20%, 1000 VDCW; sim to Sprague Type 150D. C3 5496267P1 Tantalum: 1 µf ±20%, 50 VDCW. C3 5496267P1 Tantalum: 1 µf ±20%, 50 VDCW; sim to Sprague Type 150D. C3 5496267P1 Tantalum: 1 µf ±20%, 50 VDCW; sim to Sprague Type 150D. C3 5496267P1 Tantalum: 1 µf ±20%, 50 VDCW; sim to Sprague Type 150D. C3 5496267P1 Tantalum: 1 µf ±20%, 50 VDCW; sim to Sprague Type 150D. C3 5496267P1 Tantalum: 1 µf ±20%, 50 VDCW; sim to Sprague Type 150D. C3 5496267P1 Tantalum: 1 µf ±20%, 50 VDCW; sim to Sprague Type 150D. C3 5496267P1 Tantalum: 1 µf ±20%, 50 VDCW; sim to Sprague Type 150D. C3 5496267P1 Tantalum: 1 µf ±20%, 50 VDCW; sim to Sprague Type 150D. C3 5496267P1 Tantalum: 1 µf ±20%, 50 VDCW; sim to Sprague Type 150D. C3 5496267P1 Tantalum: 2 2 µf ±20%, 1000 VDCW; sim to Sprague T				thru
C2 5496267P14 TRAILBUR: 15 # 120%, 20 VDCW; sim to Sprague Type 150D. C3 19A116080P9 Polyester: 0.22 # f 120%, 50 VDCW. C4 5496267P1 Trailbur: 15 # f 20%, 20 VDCW; sim to Sprague Type 150D. C5 5496267P1 Trailbur: 15 # f 20%, 6 VDCW; sim to Sprague Type 150D. C6 19A116080P5 Polyester: .047 # f 120%, 50 VDCW. C1 19A116080P5 Polyester: .047 # f 120%, 1000 VDCW; sim to MNC Type JF Discap. C1 2 5496267P13 Trailbur: 2.2 # f 20%, 20 VDCW; sim to Sprague Type 150D. C1 2 5494481P111 Ceramic disc: .001 pf 120%, 1000 VDCW; sim to RNC Type JF Discap. C1 3 5494481P111 Ceramic disc: .001 pf 120%, 1000 VDCW; sim to RNC Type JF Discap. C1 19A116080P5 Polyester: .047 # f 120%, 50 VDCW. C1 19A116080P5 Polyester: .047 # f 120%, 1000 VDCW; sim to RNC Type JF Discap. C1 19C1 S496267P1 Trailbur: 22 # f 120%, 1000 VDCW; sim to Sprague Type 150D. C1 29C1 S496267P1 Trailbur: 22 # f 120%, 1000 VDCW; sim to Sprague Type 150D. C2 3 Trailbur: 22 # f 120%, 15 VDCW; sim to Sprague Type 150D. C2 3 S496267P10 Trailbur: 22 # f 120%, 15 VDCW; sim to Sprague Type 150D. C2 5496267P10 Trailbur: 22 # f 120%, 1000 VDCW; sim to Sprague Type 150D. C2 5496267P10 Trailbur: 22 # f 120%, 1000 VDCW; sim to Sprague Type 150D. C3 5496267P1 Trailbur: 22 # f 120%, 1000 VDCW; sim to Sprague Type 150D. C3 5496267P1 Trailbur: 22 # f 120%, 1000 VDCW; sim to Sprague Type 150D. C3 5496267P1 Trailbur: 47 # f 120%, 50 VDCW; sim to Sprague Type 150D. C3 5496267P1 Trailbur: 48 # f 120%, 50 VDCW; sim to Sprague Type 150D. C3 5496267P1 Trailbur: 48 # f 120%, 50 VDCW; sim to Sprague Type 150D. C3 5496267P1 Trailbur: 48 # f 120%, 50 VDCW; sim to Sprague Type 150D. C3 5496267P1 Trailbur: 52 # f 120%, 20 VDCW; sim to Sprague Type 150D. C3 5496267P1 Trailbur: 52 # f 120%, 20 VDCW; sim to Sprague Type 150D. C3 5496267P1 Trailbur: 52 # f 120%, 20 VDCW; sim to Sprague Type 150D. C3 5496267P1 Trailbur: 52 # f 120%, 20 VDCW; sim to Sprague Type 150D. C3 5496267P1 Trailbur: 52 # f 120%, 20 VDCW; sim to Sprague Type 150D. C3 5496267P1 Trailbur: 52 # f 120%, 20 VDCW; sim to Sprague Typ	Cl	5496267P120	Tantalum: 47 µf ±20%, 35 VDCW; sim to Sprague Type 150D.	1
C3	C2	5496267P14	Tantalum: 15 µf ±20%, 20 VDCW; sim to	1
C4	СЗ	19A116080P9		
C30	C4	5496267P14	Tantalum: 15 µf ±20%, 20 VDCW; sim to	1
C10	thru	5496267P1	Tantalum: 6.8 µf ±20%, 6 VDCW; sim to	
C12 5496267P13 Tantalum: 2.2 \(\text{if } \text{200}\), 35 VDCW; sim to Sprague Type 150D. C13 5494481P111 Ceramic disc: .001 \(\text{pf } \text{200}\), 1000 VDCW; sim to Sprague Type 150D. C14 19A116080P5 Polyster: .047 \(\text{pf } \text{200}\), 1000 VDCW; sim to RMC Type JF Discap. C15 5494481P111 Ceramic disc: .001 \(\text{pf } \text{200}\), 1000 VDCW; sim to RMC Type JF Discap. C16 C17 S496267P17 Tantalum: 1 \(\text{pf } \text{200}\), 35 VDCW; sim to Sprague Type 150D. C19 S496267P10 Tantalum: 22 \(\text{pf } \text{200}\), 15 VDCW; sim to Sprague Type 150D. C20 19A116080P5 Polyster: .047 \(\text{pf } \text{200}\), 50 VDCW. C21 S496267P10 Tantalum: 22 \(\text{pf } \text{200}\), 15 VDCW; sim to Sprague Type 150D. C22 S496267P10 Tantalum: 22 \(\text{pf } \text{200}\), 15 VDCW; sim to Sprague Type 150D. C23 S496481P11 Ceramic disc: .001 \(\text{pf } \text{200}\), 1000 VDCW; sim to RMC Type JF Discap. C32 S496267P2 Tantalum: 47 \(\text{pf } \text{200}\), 35 VDCW; sim to Sprague Type 150D. C33 S496267P17 Tantalum: 47 \(\text{pf } \text{200}\), 35 VDCW; sim to Sprague Type 150D. C34 S496267P17 Tantalum: 47 \(\text{pf } \text{200}\), 35 VDCW; sim to Sprague Type 150D. C35 19A116080P103 Polyster: .022 \(\text{pf } \text{200}\), 35 VDCW; sim to Sprague Type 150D. C36 S496267P11 Tantalum: 22 \(\text{pf } \text{200}\), 35 VDCW; sim to Sprague Type 150D. C37 Tantalum: 2.2 \(\text{pf } \text{200}\), 35 VDCW; sim to Sprague Type 150D. C38 S496267P11 Tantalum: 2.2 \(\text{pf } \text{200}\), 30 VDCW; C39 Tantalum: 2.2 \(\text{pf } \text{200}\), 30 VDCW; C39 Tantalum: 2.2 \(\text{pf } \text{200}\), 30 VDCW; C30 S496267P13 Tantalum: 2.2 \(\text{pf } \text{200}\), 30 VDCW; C31 S496267P13 Tantalum: 2.2 \(\text{pf } \text{200}\), 30 VDCW; C31 S496267P13 Tantalum: 2.2 \(\text{pf } \text{200}\), 30 VDCW; C31 S496267P13 Tantalum: 2.2 \(\text{pf } \text{200}\), 30 VDCW; C31 S496267P13 Tantalum: 2.2 \(\text{pf } \text{200}\), 30 VDCW; C31 S496267P13 Tantalum: 2.2 \(\text{pf } 20		19A116080P5	Polyester: .047 µf ±20%, 50 VDCW.	Q22
C12 S496267P13 Tantalum: 2.2 μf ±20%, 20 VDCW; sim to Sprague Type 150D.	C11	5494481P111	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to	thru
C13	C12	5496267P13	Tantalum: 2.2 μf ±20%, 20 VDCW; sim to	
C14 19A116080P5 Polyester: .047 µf ±20%, 50 VDCW. C15 5494481P111 Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. C17 5496267P17 Tantalum: 1 µf ±20%, 35 VDCW; sim to Sprague Type 150D. C19 5496267P10 Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D. C20 19A116080P5 Polyester: .047 µf ±20%, 50 VDCW. C21 5496267P10 Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D. C22 5496267P10 Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D. C23 5494481P111 Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. C31 5496267P2 Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague Type 150D. C33 5496267P17 Tantalum: 1 µf ±20%, 35 VDCW; sim to Sprague Type 150D. C34 5496267P11 Tantalum: 1 µf ±20%, 35 VDCW; sim to Sprague Type 150D. C35 19A116080P103 Polyester: .022 µf ±10%, 50 VDCW. C36 5496267P13 Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C37 Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C38 19A116080P103 Polyester: .022 µf ±10%, 50 VDCW. C39 Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C39 Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C30 Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C31 19A116250P1 Silicon. C32 Tantalum: 2.2 µf ±20%, 30 VDCW; sim to Sprague Type 150D. C33 Tantalum: 30 µf ±20%, 30 VDCW; sim to Sprague Type 150D. C34 Tantalum: 30 µf ±20%, 30 VDCW; sim to Sprague Type 150D. C35 19A116080P103 Polyester: .022 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C36 5496267P13 Silicon. C67 Tantalum: 30 µf ±20%, 30 VDCW; sim to Sprague Type 150D. C78 Tantalum: 40 µf ±20%, 30 VDCW; sim to Sprague Type 150D. C89 Tantalum: 50 µf ±20%, 30 VDCW; sim to Sprague Type 150D. C80 Tantalum: 50 µf ±20%, 30 VDCW; sim to Sprague Type 150D. C81 Tantalum: 60 µf ±20%, 30 VDCW; sim to Sprague Type 150D. C81 Tantalum: 1 µf ±20%, 30 VDCW; sim to Sprague Type 150D. C82 Tantalum: 1 µf ±20%, 30 VDCW; sim to Sprague Type 150D. C83 Tantalum: 1 µf ±20%, 30 VDCW; sim to Sprague Type 150D. C84 Tantalum: 1 µf ±20%, 30 VD	C13	5494481P111	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to	
C15 and S494481P111 Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Q39 Q40 Q40 Q41 Q41 Q41 Q42 Q42 Q42 Q42 Q42 Q42 Q42 Q42 Q42 Q43 Q4	C14	19A116080P5	•	
C17 and C18 C19 5496267P10 Tantalum: 1 µf ±20%, 35 VDCW; sim to Sprague Type 150D. C20 19A116080P5 Polyester: .047 µf ±20%, 50 VDCW. R1 R2 C22 5496267P10 Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D. C23 Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D. C24 C25 C25 C26 C27 C28 C29 S496267P10 Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D. C30 C31 C31 C32 C496267P2 Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague Type 150D. C33 S496267P17 Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague Type 150D. C34 S496267P17 Tantalum: 68 µf ±20%, 15 VDCW; sim to Sprague Type 150D. C35 S496267P11 Tantalum: 68 µf ±20%, 15 VDCW; sim to Sprague Type 150D. C36 S496267P13 Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C37 Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C38 C496267P13 Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C39 C40 C41 C41 C42	and	5494481P111	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to	
Sprague Type 150D. Q41 Q42		E 406067777		Q40
C19	and	0490207P17	Tantalum: 1 µf ±20%, 35 VDCW; sim to Sprague Type 150D.	1
C20 and C21 C21 C22 S496267P10 Tantalum: 22 \(\pi f \) ±20%, 15 VDCW; sim to Sprague Type 150D. R3 R5 and R6 R6 R7 R7 R8 R7 R8 R8 R8 R8	C19	5496267P10	Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D.	Q42
S496267P10 Tantalum: 22 μf ±20%, 15 VDCW; sim to Sprague Type 150D. R3	and	19A116080P5	Polyester: .047 µf ±20%, 50 VDCW.	R1
Sprague Type 150D. R5 R5 R6 RMC Type JF Discap. R5 R6 RMC Type JF Discap. R7 R8 R7 Sprague Type 150D. R8 R7 R8 R8 R9 R9 R9 R9 R9 R9		5496267P10	Tantalum: 22 μf ±20%. 15 VDCW: sim to	- 1
RMC Type JF Discap. RMC RMC Type JF Discap. RMC	C23	5494481P111	Sprague Type 150D.	
Sprague Type 150D. R8	thru			
C33	C32	5496267P2	Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague Type 150D.	
Sprague Type 150D. R11	C33	5496267P17		1
C35 19A116080P103 Polyester: .022 μf ±10%, 50 VDCW. C36 5496267P13 Tantalum: 2.2 μf ±20%, 20 VDCW; sim to Sprague Type 150D. CR1 19A115250P1 Silicon. CR50 19A115250P1 Silicon. R17 20ACKS AND RECEPTACLES	C34	5496267P111		1
C36	C35	19A116080P103	Polyester: .022 µf ±10%, 50 VDCW.	1
CR1 thru CR50 thru CR50 thru CR53 19A115250P1 Silicon. Silicon. Silicon. Silicon. Silicon. Silicon. Silicon. Silicon. Silicon. CR50 thru CR53 A033513P4 Contact, electrical: sim to Bead Chain L93-3. ER21 and R22 Silicon. R16 R17 R16 R17 R17 R18 R19 R20 R20 R21 R21 R22 R23 R23 R23 R23 R23 R23 R24 Sim to Bead Chain L93-3. R23 R24 R25 R25 R25 R26 R27 R27 R28 R28 R28 R29 R29 R29 R29 R20 R20 R21 R21 R22 R23 R23 R23 R23 R23 R23 R24 R25 R25 R25 R25 R26 R27 R27 R28 R28 R29 R29 R29 R29 R29 R29 R29 R29 R20 R20 R20 R21 R21 R22 R23 R23 R23 R23 R23 R24 R25 R25 R25 R25 R25 R26 R26 R27 R27 R28 R28 R29	C36	5496267P13	Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D.	1
CR1			DIODES AND RECTIFIERS	- 1
R17	thru	19Al15250Pl		1
## CR53 The CR53 R18 R19		19411525001	Silicon	
R20	thru	10011023081	Jiiiou.	R18
J1 thru 4033513P4 Contact, electrical: sim to Bead Chain L93-3. R21 and R22 J9 thru 4033513P4 Contact, electrical: sim to Bead Chain L93-3. R23 and R24 J38 thru 4033513P15 Contact, electrical: sim to Bead Chain R40-1A. R25 and R25 and R25			JACKS AND RECEPTACLES	
J9 thru J37	thru	4033513P4	Contact, electrical: sim to Bead Chain L93-3,	R21
J38 4033513P15 Contact, electrical: sim to Bead Chain R40-1A. R25 J45 R25	J9 thru	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	R22 R23 and
1 I R26	J38 thru	4033513P15	Contact, electrical: sim to Bead Chain R40-1A.	R25 and
				1

Section Computation Section		SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
March Marc					R27	3R152P472J	Composition: 4700 ohms ±5%, 1/4 w.	R85	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w.
Secondary Company Co		Ql thru	19A115889P1	Silicon, NPN; sim to Type 2N2712.	R28	3R152P182J	Composition: 1800 ohms ±5%, 1/4 w.	R86	3R152P303J	
1.		Q3		İ		3R152P223K	Composition: 22,000 ohms ±10%, 1/4 w.	R87	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w.
March Marc		1	ł .	Silicon, NPN; sim to Type 2N3053.					3R152P163J	Composition: 16,000 ohms ±5%, 1/4 w.
State		thru	19A115889P1	Silicon, NPN; sim to Type 2N2712.	R33	3R152P472K	Composition: 4700 ohms $\pm 10\%$, $1/4$ w.			
March Marc					1			R92	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w.
Mail								R93	3R152P303J	Composition: 30,000 ohms ±5%, 1/4 w.
1.00 1.00		thru	19A115123P1	Silicon, NPN; sim to Type 2N2712.	1	1		R94	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w.
15 10 10 10 10 10 10 10	•		10411520002	Silicon NPN, cim to Thurs 000000		I			3R152P163J	Composition: 16,000 ohms ±5%, 1/4 w.
Section Sect			1	1	· ·	l	· ·	1 1		
Col.			1	l '	1	į.		11	1	Composition: 3300 ohms ±5%, 1/4 w.
Column C			i .	i	' I	1	1		1	Composition: 10,000 ohms ±5%, 1/4 w.
10 10 10 10 10 10 10 10	•		1	l '		ł	·	thru	3R152P222J	Composition: 2200 ohms ±5%, 1/4 w.
24 1841-185-196 1811-066-196			1	1	 	1		1 1		
14 to 0	•		1	· .				thru	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.
1.0 1.0			1			1		1		
10 10 10 10 10 10 10 10				· ·		1		1 1	1	
California Cal	; sim to	thru		,,,		1		I 1	i	· · · · · · · · · · · · · · · · · · ·
Table	0	Q35	19A115562P2	Silicon, PNP.	1	I	· ·	111	1	·
1.0 1.0		Q36	19A115123P1			I	<u>'</u>		1	· '
1	, sim to	Q37	19A115562P2		 	1	· ·	1	l	· · · · · · · · · · · · · · · · · · ·
1		Q38	19A115123P1	· .			1	11	1	,
Column	; sim to	Q39	19A115562P2			1	•	RIIS	3R152P753J	Composition: 75,000 ohms ±5%, 1/4 w.
012 10113123P 20113123P		Q40	19A115123P1	Silicon, NPN; sim to Type 2N2712.	and		20,000 0000 20,000 1/4 #.	!		
1		Q41	19A115562P2	· · · · · · · · · · · · · · · · · · ·	 	3R152P513J	Composition: 51.000 ohms +5% 1/4 w] m,		
Bill 30779204 Composition 2000 dams 55, 1/4 v. 2000 dams 15, 1/4 v. 2000 dams		Q42	19A115123P1	Silicon, NPN; sim to Type 2N2712.			· '	"		
ST STITEMEN Composition: 100 chas 155, 1/4 v. 55 SHISPENIA Composition: 130 chas 155, 1/4 v. 55 SHISPENIA Composition: 130 chas 155, 1/4 v. 55 SHISPENIA Composition: 130 chas 155, 1/4 v. 56 SHISPENIA Composition: 130 chas 155, 1/4 v. 57 SHISPENIA Composition: 130 chas 155, 1/4 v. 58 SHISPENIA SHISPENIA Composition: 130 chas 155, 1/4 v. 58 SHISPENIA Co			1		R56	1		11		auturarens
2 39152011E Composition: 130 cata 155, 1/4 v. 180 38152011E Composition: 130 cata 155, 1/4 v. 180 381520011E Composition: 130 cata 155, 1/4 v. 180 381520011E Composition: 130 cata 155, 1/4 v. 180 381520011E Composition: 130 cata 155, 1/4 v. 180 Composition: 130 cata 155, 1/4 v.					R57	3R152P103J	•		190307114022036	3.2.1.01.7.0
Sample S			1	· ·	R58	3R152P513J	-	1 1		
All to State Sta		i I	1	· '	R59	3R152P103J	•			100,000 pr 12%, 100 vicw.
State Composition: 2000 chas 255, 1/4 v. 2000 20		l i l	1	1	R60	3R152P513J	· ·	ł I		DIODES AND RECTIFIERS
R7 381527013 Composition: 2000 ohms 155, 1/4 v. R92	; sim to	and	3R152P433J	Composition: 43,000 ohms ±5%, 1/4 w.	R61	3R152P202J	· ·		19A115250P1	Silicon.
R8			3915399031	Composition 2000 share 15% 2.44		3R152P563J				
No		1 1	1	· ·						
RIO 3R152P103J Composition: 1000 chas 255, 1/4 v. RI1 3R152P103J Composition: 1000 chas 255, 1/4 v. RI2 3R152P10J Composition: 300 chas 255, 1/4 v. RI3 3R152P10J Composition: 300 chas 255, 1/4 v. RI4 3R152P10J Composition: 300 chas 255, 1/4 v. RI5 3R152P20J Composition: 300 chas 255, 1/4 v. RI6 3R152P10J Composition: 300 chas 255, 1/4 v. RII 4R1 Composition: 300 chas 255, 1/4 v. RII 4R1 Composition: 300 chas 255, 1/4 v. RII 4R1 Composition: 300 chas 255, 1/4 v. RI				ĺ.	R64	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w.	L1	19C300501G410	Ferrite coil.
Nii			i	· ·	R66	3R152P303J	Composition: 30,000 ohms ±5%, 1/4 w.	L2	19C300501G411	Ferrite coil.
R12 3R152P511J Composition: 510 chas ±58, 1/4 w. R13 3R152P511J Composition: 510 chas ±58, 1/4 w. R14 3R152P512J Composition: 300 chas ±58, 1/4 w. R15 3R152P512J Composition: 2400 chas ±58, 1/4 w. R16 3R152P52J Composition: 2400 chas ±58, 1/4 w. R17 R18 R19 3R152P52J Composition: 1000 chas ±58, 1/4 w. R18 3R152P52J Composition: 1000 chas ±58, 1/4 w. R19 3R152P52J Composition: 1000 chas ±58, 1/4 w. R19 3R152P52J Composition: 010 chas ±58, 1/4 w. R10 3R152P52J Composition: 010 chas ±58, 1/4 w. R10 3R152P52J		1 1	1	•	R68	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.			
R13 Sal52P301J Composition: 300 chas ±58, 1/4 w. R14 3al52P461J Composition: 160 chas ±58, 1/4 w. R15 3al52P42J Composition: 2000 chas ±55, 1/4 w. R16 3al52P42J Composition: 000 chas ±55, 1/4 w. R17 3al52P202J Composition: 000 chas ±55, 1/4 w. R17 3al52P302J Composition: 000 chas ±55, 1/4 w. R19 3al52P302J Composition: 0.12 megcha ±105, 1/4 w. R20 3al52P33J Composition: 0.12 megcha ±105, 1/4 w. R21 3al52P33J Composition: 0.12 megcha ±105, 1/4 w. R22 3al52P33J Composition: 18,000 chas ±55, 1/4 w. R23 3al52P33J Composition: 0.12 megcha ±105, 1/4 w. R23 3al52P33J Composition: 0.12 megcha ±105, 1/4 w. R21 3al52P33J Composition: 0.12 megcha ±105, 1/4 w. R22 3al52P33J Composition: 0.12 megcha ±105, 1/4 w. R23 3al52P33J Composition: 0.12 megcha ±105, 1/4 w. R24 3al52P33J Composition: 0.12 megcha ±105, 1/4 w. R25 3al52P33J Composition: 0.12 megcha ±105, 1/4 w. R28 3al52P33J Composition: 0.12 megcha ±105, 1/4 w. R28 3al52P303J Composition: 0.12 megcha ±105, 1/4 w. R28 3al52P303J Composition: 0.10 megcha ±105, 1/4 w. R28 3al52P303J Composition: 0.10 megcha ±105, 1/4 w. R28 3al52P303J Composition: 0.10 megcha ±105, 1/4 w. R29 3al52P303J Composition: 0.10 megcha ±105, 1/4 w. R29 3al52P303J Composition: 0.10 megcha ±105, 1/4 w. R20 3al52P303J Composition: 0.10 megcha ±105, 1/4 w. R21 3al52P303J Composition: 0.10 megcha ±105, 1/4 w. R22 3al52P303J Composition: 0.10 megcha ±105, 1/4 w. R20 3al52P303J Composition: 0.10 megcha ±105, 1/4 w. R20 3al52P303J Composition: 0.10 megcha ±105, 1/4 w. R21 3al52P303J Composition: 0.10 megcha ±105, 1/4 w. R22 3al52P303J Composition: 0.10 megcha ±105, 1/4 w. R22 3al52P303J Composition: 0.10 meg		i i	1		R69	3R152P302J	Composition: 3000 ohms ±5%, 1/4 w.	VR1	4036887P3	
R14 3R152P161J Composition: 160 cham into the composition: 2400 cham into the composition: 240	0	ł I	1	· · · · · · · · · · · · · · · · · · ·	R70	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w.	VR2	4036887P2	Silicon, Zener.
R15 3R152P4242 Composition: 2400 cham ±55, 1/4 w. R16 3R152P6221 Composition: 6200 cham ±55, 1/4 w. R17 and R18 R19 3R152P1021 Composition: 0.12 megcha ±105, 1/4 w. R19 3R152P1021 Composition: 0.12 megcha ±105, 1/4 w. R19 3R152P1021 Composition: 0.12 megcha ±105, 1/4 w. R19 3R152P1022 Composition: 0.12 megcha ±105, 1/4 w. R19 3R152P1023 Composition: 0.12 megcha ±105, 1/4 w. R19 3R152P1023 Composition: 0.12 megcha ±105, 1/4 w. R19 3R152P1024 Composition: 18,000 cham ±55, 1/4 w. R19 3R152P1024 Composition: 18,000 cham ±55, 1/4 w. R19 3R152P1024 Composition: 10,000 cham ±55, 1/4 w. R10 3R152P1024 Composition: 10,000 cham ±55, 1/4 w. R10 3R152P1024 Composition: 10,000 cham ±55, 1/4 w. R10 R10 R10 R10 Composition: 10,000 cham ±55, 1/4 w. R10 R10 R10 R10 Composition: 10,000 cham ±55, 1/4 w. R10 R10 R10 Composition: 10,000 cham ±55, 1/4 w. R10 R10 R10 R10 Composition: 10,000 cham ±55, 1/4 w. R10 R10 R10 R10 Composition: 10,000 cham ±55, 1/4 w. R10 R10 R10 R10 Composition: 10,000 cham ±55, 1/4 w. R10 R10 R10 R10 Composition: 10,000 cham ±55, 1/4 w. R10		}	1		R71	3R152P303J	Composition: 30,000 ohms ±5%, 1/4 w.		4036887P4	Silicon, Zener.
R16 3R152P623/ Composition: 6200 chms ±55, 1/4 w. R17 3R152P1023/ Composition: 1000 chms ±55, 1/4 w. R18 3R152P1024 Composition: 0.12 megchm ±105, 1/4 w. R20 3R152P833/ Composition: 0.12 megchm ±105, 1/4 w. R20 3R152P833/ Composition: 68,000 chms ±55, 1/4 w. R21 3R152P833/ Composition: 18,000 chms ±55, 1/4 w. R22 R23 and R24 R24 R0-1A. R40-1A. R40-1A. R16 3R152P1023/ Composition: 6200 chms ±55, 1/4 w. R27 SR152P2033/ R78 SR152P2034 Composition: 1000 chms ±55, 1/4 w. R27 SR152P2034 Composition: 18,000 chms ±55, 1/4 w. R28 R28 R29 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R40-1A. R40-1A. R17 SR152P2034 Composition: 2000 chms ±55, 1/4 w. R28 SR152P2034 Composition: 2000 chms ±55, 1/4 w. R29 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R20 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R21 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R22 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R23 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R24 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R25 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R26 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R27 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R28 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R29 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R20 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R21 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R22 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R23 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R24 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R25 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R27 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R28 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R29 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R29 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R20 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R20 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R21 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R22 SR152P2034 Composition: 10,000 chms ±55, 1/4 w. R23 S		l 1	i	i i	R73	3R152P303J	Composition: 30,000 ohms ±5%, 1/4 w.			
Ri7 and Ri8 3R152P102J Composition: 1000 ohms ±5%, 1/4 w. Ri9 3R152P124K Composition: 0.12 megohn ±10%, 1/4 w. Ri9 3R152P183J Composition: 68,000 ohms ±5%, 1/4 w. Ri9 3R152P183J Composition: 68,000 ohms ±5%, 1/4 w. Ri9 3R152P183J Composition: 18,000 ohms ±5%, 1/4 w. Ri9 3R152P183J Composition: 18,000 ohms ±5%, 1/4 w. Ri9 3R152P183J Composition: 18,000 ohms ±5%, 1/4 w. Ri9 3R152P183J Composition: 3000 ohms ±5%, 1/4 w. Ri9 3R152P183J Composition: 3000 ohms ±5%, 1/4 w. Ri9 3R152P183J Composition: 3000 ohms ±5%, 1/4 w. Ri9 3R152P183J Composition: 10,000 ohms ±5%, 1/4 w. Ri9 3R152P183J Composition: 10,		l I	1	1	R74	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w.			
and R18 R19 SR152P183J Composition: 0.12 megohm ±10%, 1/4 w. R76 R77 R78 R78 R78 R78 R78 R78 R78 R78 R78		R17	1	1		3R152P303J	Composition: 30,000 ohms ±5%, 1/4 w.			MISCELLANEOUS
R19 3R152P124X Composition: 0.12 megoha ±105, 1/4 w. R20 3R152P83J Composition: 68,000 ohms ±5\$, 1/4 w. R21 3R152P183J Composition: 18,000 ohms ±5\$, 1/4 w. R22 3R152P183J Composition: 18,000 ohms ±5\$, 1/4 w. R23 and R24 R24 R25 R25 R25 R26 R26 R26 R26 R26 R27 R26 R26 R27 R26								11	4036555P1	Insulator, washer: nvlon. (Used with 04 9 1
R20 3R152P683J Composition: 68,000 ohms ±5%, 1/4 w. R21 3R152P183J Composition: 18,000 ohms ±5%, 1/4 w. R22 R23 R23 R34 R40-lA. R40-lA. R40-lA. R40-la. R20 3R152P683J Composition: 3000 ohms ±5%, 1/4 w. R78 R79 R80 R8152P103J Composition: 2000 ohms ±5%, 1/4 w. R80 R81 R81 R82 R83 R82 R83 R82 R83 R82 R83 R84 R84 R80 R81 R82 R83 R83 R852P103J Composition: 2000 ohms ±5%, 1/4 w. R80 R81 R82 R83 R82 R83 R83 R852P103J Composition: 2000 ohms ±5%, 1/4 w. R80 R81 R82 R83 R82 R83 R83 R852P103J Composition: 2000 ohms ±5%, 1/4 w. R80 R81 R82 R83 R82 R83 R83 R852P103J Composition: 2000 ohms ±5%, 1/4 w. R80 R81 R82 R83 R82 R83 R83 R82 R83 R83 R83 R83 R84 R84 R80 R80 R81 R82 R83 R83 R82 R83 R83 R83 R83 R83 R84 R84 R80 R80 R81 R84 R84 R80 R80 R81 R84 R84 R80 R81 R82 R83 R852P103J Composition: 2000 ohms ±5%, 1/4 w. R80 R81 R82 R83 R83 R82 R83		R19	3R152P124K	Composition: 0,12 megohm ±10%, 1/4 w.	R77	3R152P913J	Composition: 91,000 ohms ±5%, 1/4 w.			16, 18, 20, 22, 35, 37, 39, 41).
n L93-3. R21 and R24 n R40-1A. R25 and R26 R25 and R26 R26 R25 and R26 R26 R26 R26 R27 R27 R28 R29		R20	3R152P683J		R78	3R152P302J	Composition: 3000 ohms ±5%, 1/4 w.			
n L93-3. R22 R23 And R24 n R40-1A. R25 And R26 R25 And R26 R26 R3152P102K Composition: 2000 ohms ±5%, 1/4 w. Composition: 1000 ohms ±10%, 1/4 w. R81 R82 R82 R82 R82 R81 R82 R82 R83 And R84 R84 R84 R85 And R84 R84 R85 And R84 R85 And R84 R87 And R84 R87 And R84 R87 And R84 R88 R8152P103J Composition: 10,000 ohms ±5%, 1/4 w. Composition: 10,000 ohms ±5%, 1/4 w. Composition: 16,000 ohms ±5%, 1/4 w. Composition: 16,000 ohms ±5%, 1/4 w. Composition: 16,000 ohms ±5%, 1/4 w.	n L93-3.		3R152P183J			ı	Composition: 200 ohms ±5%, 1/4 w.	!		
R23 and R24 R25 and R26 R26 R27 R28 R28 R29 R29 R29 R29 R29 R29		R22				3R152P163J	Composition: 16,000 ohms ±5%, 1/4 w.	l I		
R24 R24 R25 and R26 R3152P102K Composition: 1000 ohms ±10%, 1/4 w. R82 R83 and R84 R84 R84 R85 SR152P163J Composition: 2000 ohms ±5%, 1/4 w. Composition: 16,000 ohms ±5%, 1/4 w.	n L93-3.		3R152P202J	Composition: 2000 ohms ±5%, 1/4 w	!		Composition: 10,000 ohms ±5%, 1/4 w.			
R25 and R26 Composition: 1000 ohms ±10%, 1/4 w. and R84						į.	Composition: 2000 ohms ±5%, 1/4 w.			
	n R40-1A.		3R152P102K	Composition: 1000 ohms ±10%, 1/4 w.	and	3R152P163J	Composition: 16,000 ohms ±5%, 1/4 w.			
			1		R84					
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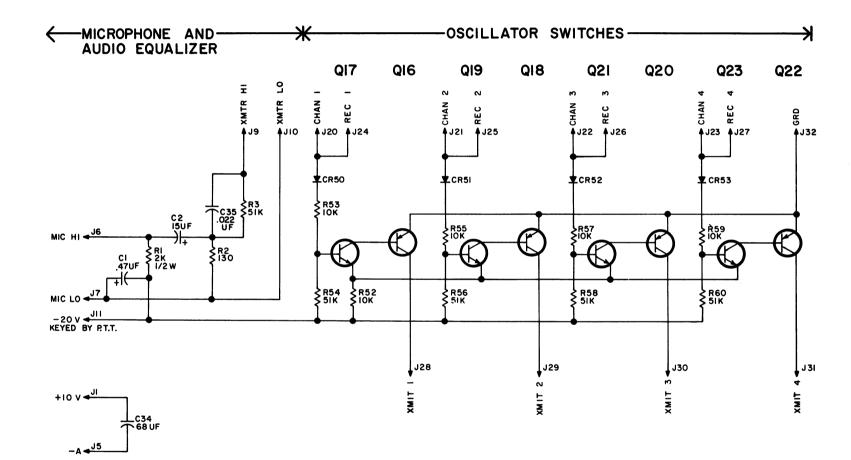
*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.



COMPONENT BOARD WITHOUT 600/1500 SIGNALLING PL-19D402713-G3

SYMBOL	G-E PART NO.	DESCRIPTION
C1	5496267-P115	Tantalum, dry solid: 47 µf ±20%, 20 VDCW; sim to Sprague Type 150D.
C2	5496267-P14	Tantalum, dry solid: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.
C34	5496267-P111	Tantalum, dry solid: 68 µf ±20%, 15 VDCW; sim to Sprague Type 150D.
C35	19B209243-P103	Polyester: .022 µf ±10%, 40 VDCW.
CR50 thru CR53	19A115250-P1	DIODES AND RECTIFIERS Silicon,
Jl thru J7	4033513-P4	JACKS AND RECEPTACLES Contact, electrical: sim to Bead Chain L93-3.
J9 thru J37	4033513-P4	Contact, electrical: sim to Bead Chain L93-3.
		TRANSISTORS
Q16	19A115562-P2	Silicon, PNP.
Q17	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
Q18	19A115562-P2	Silicon, PNP.
Q19	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
Q20	19A115562-P2	Silicon, PNP.
Q21	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
Q22	19A115562-P2	Silicon, PNP.
Q23	19Al15123-Pl	Silicon, NPN; sim to Type 2N2712.
R1	3R77-P202J	Fixed composition: 2000 ohms ±5%, 1/2 w.
R2	3R152-P131K	Fixed composition: 130 ohms ±10%, 1/4 w.
R3	3R152-P513K	Fixed composition: 51,000 ohms ±10%, 1/4 w.
R52 and R53	3R152-P103J	Fixed composition: 10,000 ohms ±5%, 1/4 w.
R54	3R152-P513J	Fixed composition: 51,000 ohms ±5%, 1/4 w.
R55	3R152-P103J	Fixed composition: 51,000 ohms ±5%, 1/4 w. Fixed composition: 10,000 ohms ±5%, 1/4 w.
R56	3R152-P513J	Fixed composition: 51,000 ohms ±5%, 1/4 w.
R57	3R152-P103J	Fixed composition: 10,000 ohms ±5%, 1/4 w.
R58	3R152-P513J	Fixed composition: 51,000 ohms 15%, 1/4 w.
R59	3R152-P103J	Fixed composition: 10,000 ohms ±5%, 1/4 w.
R60	3R152-P513J	Fixed composition: 51,000 ohms ±5%, 1/4 w.
		MISCELLANEOUS
	4036555-P1	Insulator, washer: nylon. (Used with Q16, 18, 20, 22).

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.



WIRING DIAGRAM

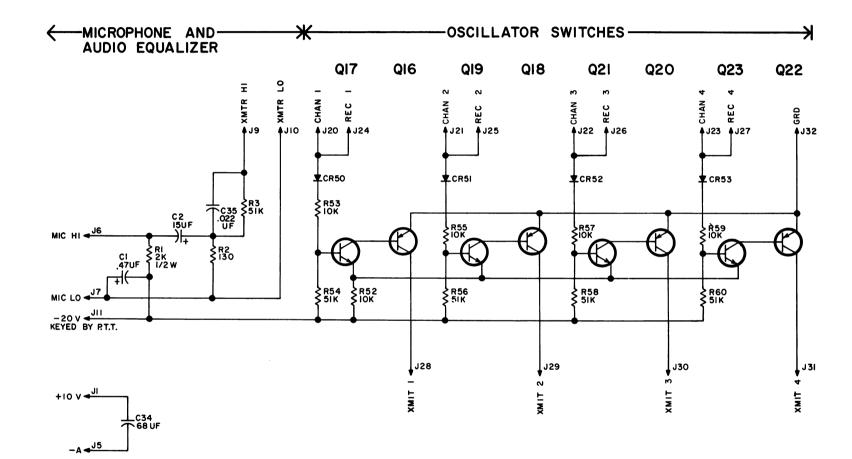
COMPONENT BOARD PL-19D402713-G3

(19C311074, Rev. 1)

COMPONENT BOARD WITHOUT 600/1500 SIGNALLING PL-19D402713-G3

SYMBOL	G-E PART NO.	DESCRIPTION
Cl	5496267-P115	Tantalum, dry solid: 47 µf ±20%, 20 VDCW; sim to Sprague Type 150D.
C2	5496267-P14	Tantalum, dry solid: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.
C34	5496267-P111	Tantalum, dry solid: 68 µf ±20%, 15 VDCW; sim to Sprague Type 150D.
C35	19B209243-P103	Polyester: .022 μf ±10%, 40 VDCW.
CR50 thru CR53	19All5250-Pl	DIODES AND RECTIFIERS
Jl thru J7	4033513-P4	JACKS AND RECEPTACLES Contact, electrical: sim to Bead Chain L93-3.
J9 thru J37	4033513-P4	Contact, electrical: sim to Bead Chain L93-3.
		TRANSISTORS
Q16	19A115562-P2	Silicon, PNP.
Q17	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
Q18	19A115562-P2	Silicon, PNP.
Q19	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
Q20	19A115562-P2	Silicon, PNP.
Q21	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
Q22	19A115562-P2	Silicon, PNP.
Q23	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
R1	3R77-P202J	Fixed composition: 2000 ohms ±5%, 1/2 w.
R2	3R152-P131K	Fixed composition: 130 ohms $\pm 10\%$, $1/4$ w.
R3	3R152-P513K	Fixed composition: 51,000 ohms ±10%, 1/4 w.
R52 and R53	3R152-P103J	Fixed composition: 10,000 ohms ±5%, 1/4 w.
R54	3R152-P513J	Fixed composition: 51,000 ohms ±5%, 1/4 w.
R55	3R152-P103J	Fixed composition: 10,000 ohms ±5%, 1/4 w.
R56	3R152-P513J	Fixed composition: 51,000 ohms ±5%, 1/4 w.
R57	3R152-P103J	Fixed composition: 10,000 ohms ±5%, 1/4 w.
R58	3R152-P513J	Fixed composition: 51,000 ohms ±5%, 1/4 w.
R59	3R152-P103J	Fixed composition: 10,000 ohms ±5%, 1/4 w.
R60	3R152-P513J	Fixed composition: 51,000 ohms $\pm 5\%$, $1/4$ w.
	4036555-P1	Insulator, washer: nylon. (Used with Q16, 18, 20, 22).

^{*}COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.



WIRING DIAGRAM

COMPONENT BOARD PL-19D402713-G3

(19C311074, Rev. 1)

DECODER PL-19D402575-G1

CIRCUIT ANALYSIS

The output of the Tone Receiver consists of negative shifts or pulses which are applied to the input jacks, J4 and J6, on the Decoder. The alternating pulses applied to these two jacks trigger the Decoder bistable Q16 and Q17. Each pulse shift in the output of the Decoder bistable fires the Pulse One-Shot Multivibrator Q18-Q19. Each pulse output of the One-Shot Multivibrator shifts the state of the bit counter chain Q1-Q2, Q3-Q4, Q5-Q6, Q7 and Q8. The first pulse shifts bistable Q1-Q2, to the condition where Q1 is conducting. The second pulse shifts bistable, Q1-Q2, to the condition where Q2 conducts. Conduction of Q2 shifts the state of bistable, Q3-Q4, so The third pulse shifts the state of Q1-Q2 so Q1 conducts Q3 conducts. and does not change the state of Q3-Q4. Thus at the end of three pulses Q1, Q3, Q6 and Q8 are conducting. This results in the voltage on all legs of the diode matrix being shunted through the conducting transistors except leg number three.

The leading edge of the first pulse in the digit triggers the Intergrated Schmitt Triggers, Q20, Q21 and Q22. This circuit remains operated as long as the pulse train continues. At the end of the pulse train the circuit returns to its original state after a 145 millisecond delay.

If the number strapping in the register is correct (i.e. Pl connected to leg number three) the digit will enter the digit register and trigger the Interdigit Schmitt Triggers, Q3l and Q32, during the 145 ms. delay interval. When Q32 fires a positive potential is applied to the cathode of CR133. This prevents the Digit Reset One-Shot, Q28 and Q29 from being fired by the Intergrating Schmitt Trigger output at the end of the 145 ms. delay period. If the number strapping is incorrect the positive potential will not appear at CR133 and the Digit Reset One-Shot will fire and reset the register.

When the number strapping is correct the conduction of Q22 at the end of the 145 ms. interval cuases the Digit Counter Bistables, Q9 and Q10, to change state so Q9 is conducting. Thus the first digit of the number is registered. When any subsequent digit is incorrect the register will be cleared by the Digit Reset One-Shot since the positive potential on CR133 required to offset the negative pulse from the Intergrating Schmitt Trigger will not appear. The bit register is cleared 10 ms. after the Intergrating Schmitt Trigger returns to its normal state. The return to normal state causes the Delay One-Shot, Q23 and Q24, to pulse the bit Reset One-Shot, Q25, Q26 and Q27, thus clearing the bit register.

When all digits of the number have been registered in the digit register the transistor switch Q33 will conduct. The voltage at J14 and J15 will increase to 9 volts. The Decoder is then decoded and the voltage applied to the Logic Board, at P4. In the operation of the system this results in the audible alarm thus alerting the subscriber of an incoming call. The removal of the handset from it's cradle to answer the call supplies a negative pulse to the Bit Reset

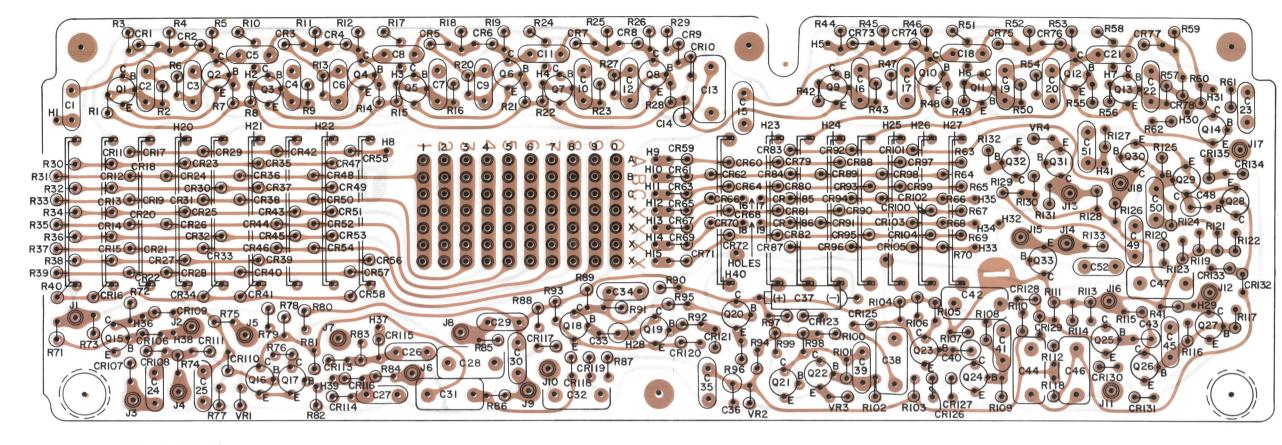
and Digit Reset One-Shot circuits thus resetting the Decoder. This pulse is inserted through Jll, Command Reset Jack.

In the event the call remains unanswered the Call Lamp stays lit and the sounder is deactivated by the digit one transmitted by the base station which clears the Decoder. Since the digit one is used to clear the decoder it cannot be used as the first Digit in the call number assigned to the mobiles. The digit one may, however, be used in any other position in the number. The use of Digit one is arbitrary in that any number, as long as it's a wrong first digit for all mobiles, can be used to accomplish the reset function.

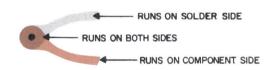
The Decoder is designed to accommodate three, five or seven digit call numbers. The wiring changes necessary to modify the board for operation with three or five digits are shown on the schematic diagram in a note.

The call number for the Mobile Unit can be changed to suit system requirements by changing the strapping to the jackfield in the center of the board. The pins are numbered from 1 to 10 and the digit leads A, B, C, X, X, X. To strap in a number connect the first digit lead (A) to one of the pin jacks in the row with the proper number for the first digit. In like fashion connect the second digit lead (B) to one of the pin jacks in the row for the second digit. (i.e., if number 8382345 is to be strapped in connect as follows: Lead A to Row 8; Lead B to row 3; Lead C to row 8; etc.).

COMMUNICATION PRODUCTS DEPARTMENT GENERAL ELECTRIC COMPANY LYNCHBURG, VIRGINIA



(19D402579, Sh. 1, Rev. 1) (19D402579, Sh. 2, Rev. 1)

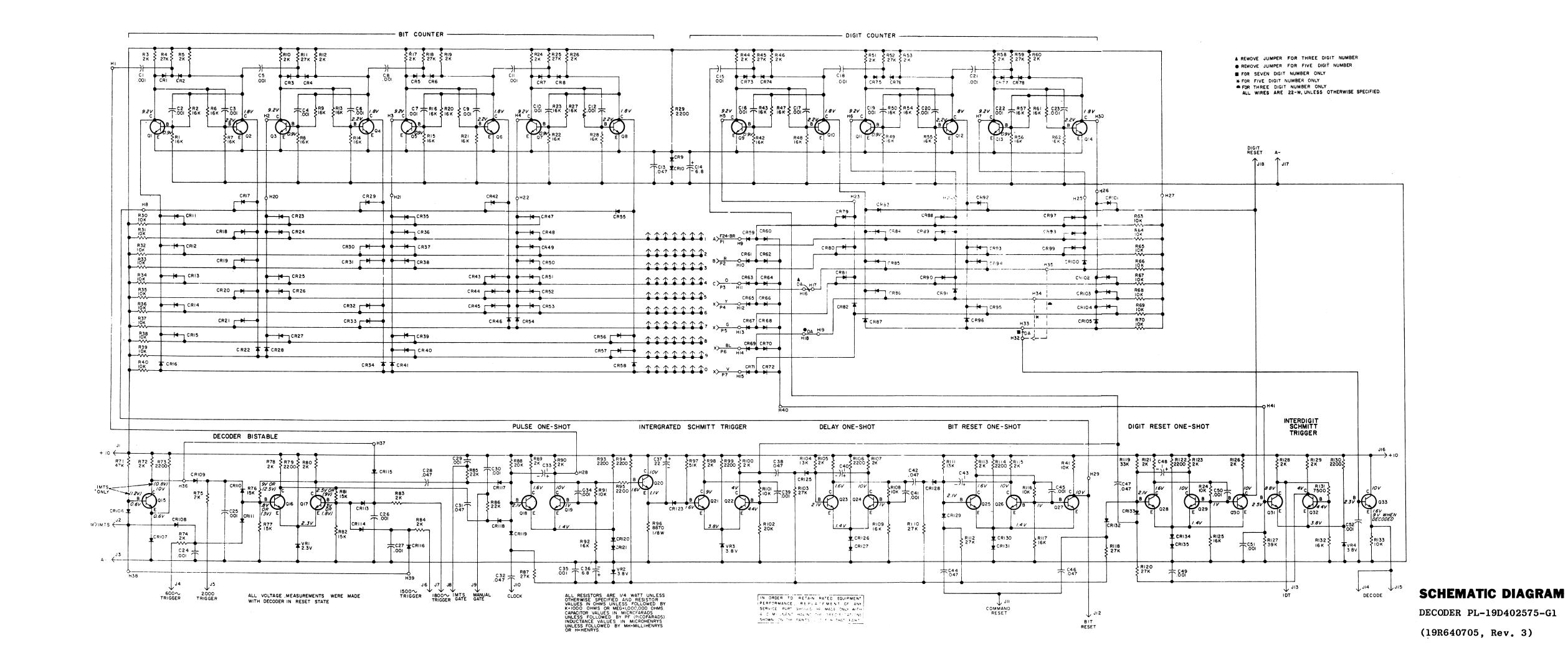


			CONNECTION	NS CHART			
FROM	WIRE IDENT.	TO	REMARKS	FROM	WIRE IDENT.	ТО	REMARKS
HI	22-W	H28		H13	F24-G	P5	LET HANG
H2		H20		H14	F24-BL	P6	LET HANG
НЗ		H21		H15	F24-V	P7	LET HANG
нч		H22		H16	DA	H17	REMOVE JUMPER FOR THREE DIGIT NUMBER
H5		H23		H18	DA	H19	REMOVE JUMPER FOR FIVE DIGIT NUMBER
Н6		H24		H26	22-W	H30	
H7		H25		H27	22-W	H31	
Н8	22-W	H29		H32	DA	Н33	FOR SEVEN DIGIT NO.
Н9	F24-BR	PI	LET HANG	H36	22-W	H37	
HIO	F24-R	P2		H38	22-W	H39	
HII	F24-0	Р3		H40	22-W	H41	
HI2	F24-Y	P4	LET HANG				

OUTLINE DIAGRAM

DECODER PL-19D402575-G1

(19D402723, Rev. 0)



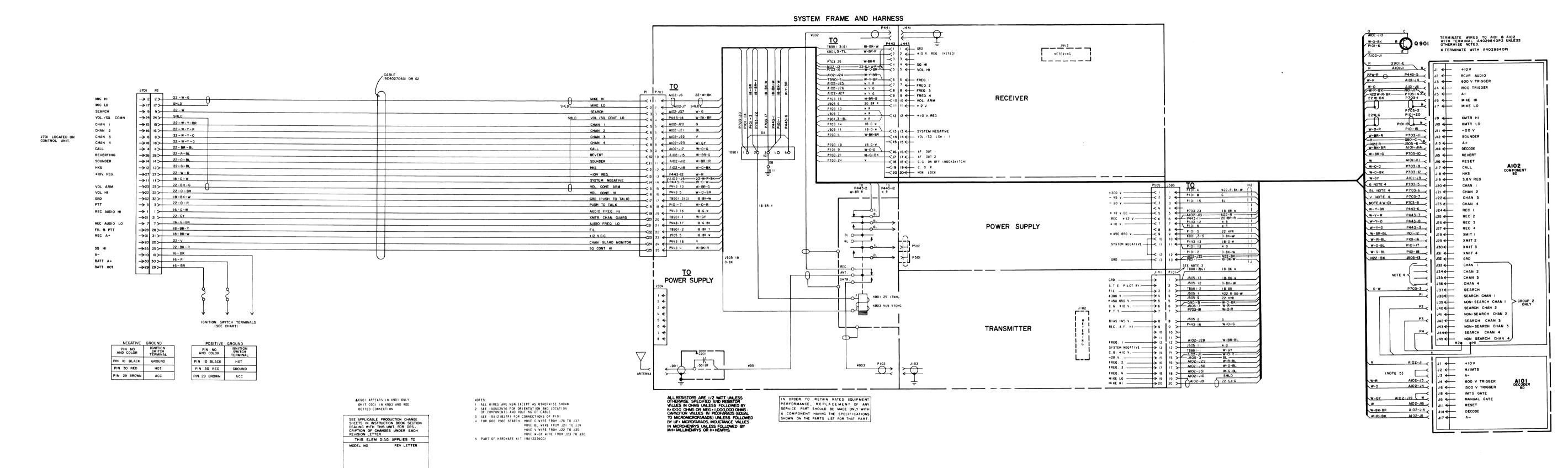
DECODER - A1603 PL-19D402575-G1

SYMBOL	G-E PART NO.	DESCRIPTION
Cl thru Cl2	5494481-P111	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C13	19B209243-P5	Polyester: .047 µf ±20%, 40 VDCW.
C14	5496267-P1	Tantalum, dry solid: 6.8 µf ±20%, 6 VDCW; sin Sprague Type 150D.
C15 thru C27	5494481-P111	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C28	19B209243-P5	Polyester: .047 µf ±20%, 40 VDCW.
C29 and C30	5494481-P111	Coramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C31 and C32	19B209243-P5	Polyester: .047 µf ±20%, 40 VDCW.
C33	5496267-P217	Tantalum, dry solid: 1 μ f \pm 10%, 35 VDCW; sim Sprague Type 150D.
C34 and C35	5494481-P111	Ceramic disc: .001 μf $\pm 20\%$, 1000 VDCW; sim to RMC Type JF Discap.
C36	5496267-P1	Tantalum, dry solid: 6.8 µf ±20%, 6 VDCW; sim Sprague Type 1500.
C37	5496267-P410	Tantalum, dry solid: 22 μ f ±5%, 15 VDCW; sim Sprague Type 150D.
C38	19B209243-P5	Polyester: .047 µf ±20%, 40 VDCW.
C39	5494481-P111	Ceramic disc: .001 μ f \pm 20%, 1000 VDCW; sim to RMC Type JF Discap.
C40	5496267-P17	Tantalum, dry solid: 1 μ f ±10%, 35 VDCW; sim Sprague Type 150D.
C41	5494481-P111	Ceramic disc: .001 μf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C42	19B209243-P5	Polyester: .047 µf ±20%, 40 VDCW.
C43	5496267-P17	Tantalum, dry solid: 1 μf $\pm 10\%$, 35 VDCW; sim Sprague Type 150D.
C44	19B209243-P5	Polyester: .047 µf ±20%, 40 VDCW.
C45	5494481-P111	Ceramic disc: .001 μf $\pm 20\%,$ 1000 VDCW; sim to RMC Type JF Discap.
C46 and C47	19B209243-P5	Polyester: .047 μ1 ±20%, 40 VDCW.
C48	5496267-P17	Tantalum, dry solid: 1 μ f \pm 10%, 35 VDCW; sim t Sprague Type 150D.
C49 thru C52	5494481-P111	Ceramic disc: .001 μf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
		DIODES AND RECTIFIERS
CR1 thru CR111	19A115250-P1	Silicon,
CR113 thru CR121	19A115250-P1	Silicon.
CR123	19A115250-P1	Silicon.
CR125 thru CR135	19A115250-P1	Silicon.

	SYMBOL	G-E PART NO	DESCRIPTION	SYMBOL	G-E PART NO	DESCRIPTION	SYMBOL	G-E PART NO	DESCRIPTION
	P1	4036634-P1				RESISTORS(Cont'd)			RESISTORS(Cont'd)
	thru P7	4030034-P1	Contact, electrical: sim to AMP 42428-2.	R51	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.	R111	3R152-P133J	Fixed composition: 13,000 ohms ±5%, 1/4 w.
				R52 R53	3R152-P273K	Fixed composition: 27,000 ohms ±10%, 1/4 w.	R112	3R152-P273K	Fixed composition: 27,000 ohms ±10%, 1/4 w.
İ	ı			R54	3R152-P202J 3R152-P163J	Fixed composition: 2000 ohms ±5%, 1/4 w.	R113	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.
				thru R57	3K152-P163J	Fixed composition: 16,000 ohms ±5%, 1/4 w.	R114	3R152-P222K	Fixed composition: 2200 ohms ±10%, 1/4 w.
1	Q1 thru Q17	19A115720-P1	Silicon, NPN.	R58	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.	R115	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.
	Q18	19A115728-P1		R59	3R152-P273K	Fixed composition: 27,000 ohms ±10%, 1/4 w.	R116	3R152-P103J	Fixed composition: 10,000 ohms ±5%, 1/4 w.
to	019	19A115720-P1	Silicon, NPN.	R60	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.	R117	3R152-P163J	Fixed composition: 16,000 ohms ±5%, 1/4 w.
- 1	thru Q22	100210720-91	Silicon, NPN.	R61	3R152-P163J	Fixed composition: 16,000 ohms ±5%, 1/4 w.	R119	3R152-P273K 3R152-P333J	Fixed composition: 27,000 ohms ±10%, 1/4 w.
	Q23	19A115728-P1	Silicon, NPN.	and R62		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	R120	3R152-P273K	Fixed composition: 33,000 ohms ±5%, 1/4 w.
a to	Q24	19A115720-P1	Silicon, NPN.	R63	3R152-P103K	Fixed composition: 10,000 ohms ±10%, 1/4 w.	R121	3R152-P202J	Fixed composition: 27,000 ohms ±10%, 1/4 w.
	Q25	19All5728-Pl	Silicon, NPN.	R70		, , , , , , ,	R122	3R152-P222K	Fixed composition: '2000 ohms ±5%, 1/4 w. Fixed composition: 2200 ohms ±10%, 1/4 w.
°	Q26	19Al15720-Pl	Silicon, NPN.	R71	3R152-P473K	Fixed composition: 47,000 ohms ±10%, 1/4 w.	R123	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.
	and Q27		,	R72	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.	R124	≸R152-P103J	Fixed composition: 10,000 ohms ±5%, 1/4 w.
.	Q28	19A115728-P1	Silicon, NPN.	R73	3R152-P222K	Fixed composition: 2200 ohms ±10%, 1/4 w.	R125	3R152-P163J	Fixed composition: 16,000 ohms 15%, 1/4 w.
'	Q29	19A115720-P1	Silicon, NPN.	R74 and	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.	R126	3R152-P202J	Fixed composition: 2000 ohms 15%, 1/4 w.
	thru Q33			R75			R127	3R152-P393K	Fixed composition: 39,000 ohms ±10%, 1/4 w.
				R76 and	3R152-P153J	Fixed composition: 15,000 ohms ±5%, 1/4 w.	R128	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.
to			RESISTORS	R77			and Rl 29		2000 Chair 10%, 1/4 W.
	R1			R78	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.	R130	3R152-P222K	Fixed composition: 2200 ohms ±10%, 1/4 w.
:0	and R2	3R152-P163J	Fixed composition: 16,000 ohms ±5%, 1/4 w.	R79	3R152-P222K	Fixed composition: 2200 ohms ±10%, 1/4 w.	R131	3R152-P752J	Fixed composition: 7500 ohms ±5%, 1/4 w.
- 1	R3	3R152-P202J		R80	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.	R132	3R152-P163J	Fixed composition: 16,000 ohms ±5%, 1/4 w.
lm to	R4	3R152-P2023 3R152-P273K	Fixed composition: 2000 ohms ±5%, 1/4 w.	R81 and	3R152-P153J	Fixed composition: 15,000 ohms ±5%, 1/4 w.	R133	3R152-P103K	Fixed composition: 10,000 ohms ±10%, 1/4 w.
to	R5	3R152-P202J	Fixed composition: 27,000 ohms ±10%, 1/4 w.	R82					
	B6	3R152-P163J	Fixed composition: 2000 ohms ±5%, 1/4 w.	R83 and	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.	1		VOLTAGE REGULATORS
	thru R9	0.202-71030	Fixed composition: 16,000 ohms ±5%, 1/4 w.	R84			VR1	4000007 -1	Lava.
°	R10	3R152-P202J	Fixed compositions, 2000 at an area	R85 and	3R152-P223J	Fixed composition: 22,000 ohms ±5%, 1/4 w.	VR2	4036887-P1 4036887-P3	Silicon, Zenere.
to	R11	3R152-P273K	Fixed composition: 2000 ohms ±5%, 1/4 w. Fixed composition: 27,000 ohms ±10%, 1/4 w.	R86			thru VR4	4036887-23	Silicon, Zenere.
.	H1.2	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.	R87	3R152-P273K	Fixed composition: 27,000 ohms ±10%, 1/4 w.			
٠	R13	3R152-P163J	Fixed composition: 16,000 ohms ±5%, 1/4 w.	R89	3R152-P203J 3R152-P202J	Fixed composition: 20,000 ohms ±5%. 1/4 w.			
	thru R16		, , , , , , , , , , , , , , , , , , , ,	and R90	3R102-F202J	Fixed composition: 2000 ohms ±5%, 1/4 w.			
to	R17	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.	R91	3R152-P103J	Fixed composition: 10,000 ohms ±5%, 1/4 w.			
ŀ	R18	3R152-P273K	Fixed composition: 27,000 ohms ±10%, 1/4 w.	R92	3R152-P163J	Fixed composition: 16,000 ohms ±5%, 1/4 w.			COMPONENT BOARD
	R19	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.	R93	3R152-P222K	Fixed composition: 2200 ohms ±10%, 1/4 w.			PL-19B205113-G1
	R20 thru	3R152-P163J	Fixed composition: 16,000 ohms ±5%, 1/4 w.	thru R95		2200 Olimb 110%, 174 W.			
	R23	1		R96	19B209050-P33	Deposited carbon: 8870 ohms ±1%, 1/8 w; sim to			JACKS AND RECEPTACLES
.	R24	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.			IRC Type DCA OF CEA-TO.	J1 thru	4033513-P4	Contact, electrical: sim to Bead Chain L93-3.
to	R25	3R152-P273K	Fixed composition: 27,000 ohms ±10%, 1/4 w.	R97	3R152-P513J	Fixed composition: 51,000 ohms ±5%, 1/4 w.	J18	ļ	
- 1	R26	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.	R98	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.			
	R27 and	3R152-P163J	Fixed composition: 16,000 ohms ±5%, 1/4 w.	R99	3R152-P222K	Fixed composition: 2200 ohms ±10%, 1/4 w.			
ļ	R28	İ		R100	3R152-P202J	Fixed composition: 2000 ohms ±5%, 1/4 w.			
	R29	3R152-P222K	Fixed composition: 2200 ohms ±10%, 1/4 w.	R101 R102	3R152-P103J	Fixed composition: 10,000 ohms ±5%, 1/4 w.	1		
	R30 thru	3R152-P103K	Fixed composition: 10,000 ohms ±10%, 1/4 w.	R102	3R152-P203J	Fixed composition: 20,000 ohms ±5%, 1/4 w.	1 1		
	R41	ļ		R104	3R152-P273K	Fixed composition: 27,000 ohms ±10%, 1/4 w.			
	R42 and	3R152-P163J	Fixed composition: 16,000 ohms ±5%, 1/4 w.	R105	3R152-P133J 3R152-P202J	Fixed composition: 13,000 ohms ±5%, 1/4 w.	1 1	-	
	R43			R106	3R152-P222K	Fixed composition: 2000 ohrs ±5%, 1/4 w.	j	1	
- 1	1 1	•	Fixed composition: 2000 ohms ±5%, 1/4 w.	R107	3R152-P202J	Fixed composition: 2200 ohms ±10%, 1/4 w.	1 1	į	
1	1		Fixed composition: 27,000 ohms ±10%, 1/4 w.		3R152-P103J	Fixed composition: 2000 ohms ±5%, 1/4 w.	1 1		
		3	Fixed composition: 2000 ohms ±5%, 1/4 w.	1 1	3R152-P163J	Fixed composition: 10,000 ohms ±5%, 1/4 w.	[[
	thru R50	3R152-P163J	Fixed composition: 16,000 ohms ±5%, 1/4 w.	1		Fixed composition: 16,000 ohms ±5%, 1/4 w.	1		
	A.3 0		1		- 1210K	Fixed composition: 27,000 ohms ±10%, 1/4 w.	i i		
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*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.







INTERCONNECTION DIAGRAM

(19R620762, Rev. 3)